

Low-Voltage CMOS Octal Buffer

With 5 V-Tolerant Inputs and Outputs (3-State, Inverting)

MC74LCX240

The MC74LCX240 is a high performance, inverting octal buffer operating from a 1.65 to 5.5 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A $V_{\rm I}$ specification of 5.5 V allows MC74LCX240 inputs to be safely driven from 5 V devices. The MC74LCX240 is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at the outputs at 3 V. The Output Enable (\overline{OE}) input, when HIGH, disables the outputs by placing them in a HIGH Z condition.

Features

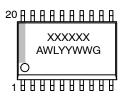
- Designed for 1.65 to 5.5 V V_{CC} Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0 \text{ V}$
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability at 3 V
- Near Zero Static Supply Current in All Three Logic States (10 μA)
 Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 100 mA
- ESD Performance:
 - ♦ Human Body Model >2000 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



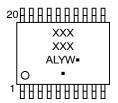


SOIC-20 WB DW SUFFIX CASE 751D TSSOP-20 DT SUFFIX CASE 948E

MARKING DIAGRAM



SOIC-20 WB



TSSOP-20

A = Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet

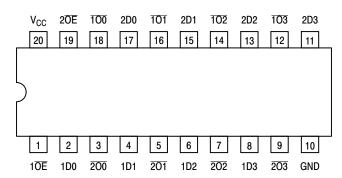
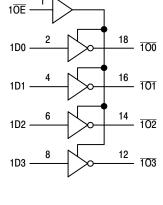


Figure 1. Pinout: 20-Lead (Top View)



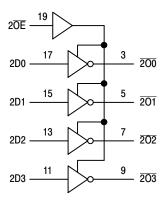


Figure 2. LOGIC DIAGRAM

PIN NAMES

Pins	Function			
nOE	Output Enable Inputs			
1Dn, 2Dn	Data Inputs			
10n, 20n	3-State Outputs			

TRUTH TABLE

Inputs		Outputs
10E 20E	1Dn 2Dn	10n, 20n
L	L	Н
L	Н	L
Н	Х	Z

H = High Voltage Level
L = Low Voltage Level
Z = High Impedance State
X = High or Low Voltage Level and Transitions
Are Acceptable; for I_{CC} reasons, DO NOT FLOAT Inputs

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{CC}	DC Supply Voltage	-0.5 to +6.5	V	
VI	DC Input Voltage (Note 1)		-0.5 to +6.5	V
	DC Output Voltage (Note 1)	Active-Mode (High or Low State)	-0.5 to V _{CC} + 0.5	
V_{O}		Tri-State Mode	-0.5 to +6.5	V
		Power-Down Mode (V _{CC} = 0 V)	-0.5 to +6.5	
I _{IK}	DC Input Diode Current	V _{IN} < GND	-50	mA
lok	DC Output Diode Current	V _{OUT} < GND	-50	mA
Io	DC Output Source/Sink Current		±50	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or Ground Pir	±100	mA	
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 secs	260	°C	
TJ	Junction Temperature Under Bias	+150	°C	
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	SOIC-20W	96	°C/W
		WQFN20	99	
		QFN20	111	
		TSSOP-20	150	
P_{D}	Power Dissipation in Still Air	SOIC-20W	1302	mW
		WQFN20	1256	
		QFN20	1127	
		TSSOP-20	833	
MSL	Moisture Sensitivity	SOIC-20W All Other Packages	Level 3 Level 1	-
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	> 2000 N/A	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. I_O absolute maximum rating must be observed.

Measured with minimum pad spacing on an FR4 board, using 76 mm-by-114 mm, 2-ounce copper trace no air flow per JESD51-7.
 HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.

RECOMMENDED OPERATING CONDITIONS

Symbol	Pa	arameter	Min	Тур	Max	Unit
V _{CC}	Supply Voltage	Operating Data Retention Only	1.65 1.5	3.3 3.3	5.5 5.5	V
VI	Digital Input Voltage		0	_	5.5	V
Vo	Output Voltage	Active Mode (High or Low State) Tri-State Mode Power Down Mode (V _{CC} = 0 V)	0 0 0	- - -	V _{CC} 5.5 5.5	٧
T _A	Operating Free-Air Temperature		-40	_	+125	°C
t _r , t _f	Input Rise or Fall Rate	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V} \\ V_{CC} = 2.3 \text{ V to } 2.7 \text{ V} \\ V_{I} \text{ from } 0.8 \text{ V to } 2.0 \text{ V}, V_{CC} = 3.0 \text{ V} \\ V_{CC} = 4.5 \text{ V to } 5.5 \text{ V} \\ \end{cases}$	0 0 0 0	- - - -	20 20 10 5	nS/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

4. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS

				T _A = -40 °0	C to +85 °C	T _A = -40 °C	to +125 °C	
Symbol	Parameter	Conditions	V _{CC} (V)	Min	Max	Min	Max	Unit
V _{IH}	High-Level Input Voltage		1.65 to 1.95	0.65 x V _{CC}		0.65 x V _{CC}		V
			2.3 to 2.7	1.7		1.7		
			2.7 to 3.6	2.0		2.0		
			4.5 to 5.5	0.7 x V _{CC}		0.7 x V _{CC}		
V _{IL}	Low-Level Input Voltage		1.65 to 1.95		0.35 x V _{CC}		0.35 x V _{CC}	V
			2.3 to 2.7		0.7		0.7	
			2.7 to 3.6		0.8		8.0	
			4.5 to 5.5		0.3 x V _{CC}		0.3 x V _{CC}	
V _{OH}	V _{OH} High-Level Output Voltage	$V_I = V_{IH}$ or V_{IL}						V
		I _{OH} = -100 μA	1.65 to 5.5	V _{CC} - 0.1	-	V _{CC} - 0.1	-	
		I _{OH} = -4 mA	1.65	1.2	-	1.2	-	
		I _{OH} = -8 mA	2.3	1.8	-	1.8	-	
		I _{OH} = −12 mA	2.7	2.2	-	2.2	-	
		I _{OH} = −16 mA	3.0	2.4	-	2.4	-	
		I _{OH} = −24 mA	3.0	2.2	-	2.2	-	
		I _{OH} = -32 mA	4.5	3.8		3.8		
V _{OL}	Low-Level	V _I = V _{IH} or V _{IL}						V
	Output Voltage	I _{OL} = 100 μA	1.65 to 5.5	-	0.1	-	0.1	
		I _{OL} = 4 mA	1.65	-	0.45	-	0.45	
		I _{OL} = 8 mA	2.3	-	0.6	-	0.6	
		I _{OL} = 12 mA	2.7	-	0.4	-	0.4	
		I _{OL} = 16 mA	3.0	_	0.4	_	0.4	
		I _{OL} = 24 mA	3.0	_	0.55	_	0.55	
		I _{OL} = 32 mA	4.5		0.6		0.6	

DC ELECTRICAL CHARACTERISTICS

				T _A = -40 °C	C to +85 °C	T _A = -40 °C	to +125 °C	
Symbol	Parameter	Conditions	V _{CC} (V)	Min	Max	Min	Max	Unit
II	Input Leakage Current	V _I = 0 to 5.5 V	3.6	-	±5.0	-	±5.0	μΑ
I _{OZ}	3-State Output Leakage Current	$V_I = V_{IH}$ or V_{IL} , $V_O = 0$ V to 5.5 V	3.6	-	±5.0	-	±5.0	μΑ
l _{OFF}	Power Off Leak- age Current	V _I = 5.5 V or V _O = 5.5 V	0	-	10	-	10	μΑ
I _{CC}	Quiescent Sup- ply Current	V _I = 5.5 V or GND	3.6	-	10	-	10	μΑ
Δl _{CC}	Increase in I _{CC} per Input	V _{IH} = V _{CC} - 0.6 V	2.3 to 3.6	-	500	-	500	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

				T _A = -40 °C	C to +85 °C	T _A = -40 °C	to +125 °C	
Symbol	Parameter	Test Condition	V _{CC} (V)	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay, D to O	See Figures 3 and 4	1.65 to 1.95	-	10.3	-	10.3	ns
			2.3 to 2.7	-	7.8	-	7.8	
			2.7	-	7.5	-	7.5	
			3.0 to 3.6	-	6.5	-	6.5	
			4.5 to 5.5	-	5.9	-	5.9	
t _{PZH} , t _{PZL}	Output Enable Time,OE to OE to O	See Figures 3 and 4	1.65 to 1.95	_	13.0	-	13.0	ns
			2.3 to 2.7	-	10.0	-	10.0	
			2.7	_	9.0	-	9.0	
			3.0 to 3.6	-	8.0	-	8.0	
			4.5 to 5.5	-	7.3	-	7.3	
t _{PHZ} , t _{PLZ}	Output Disable Time, OE to O	See Figures 3 and 4	1.65 to 1.95	_	11.0	-	11.0	ns
			2.3 to 2.7	-	8.4	-	8.4	
			2.7	-	8.0	-	8.0	
			3.0 to 3.6	-	7.0	-	7.0	
			4.5 to 5.5	-	6.0	-	6.0	
t _{OSHL} , t _{OSLH}	Output to Output Skew (Note 5)		1.65 to 1.95	-	-	-	-	ns
			2.3 to 2.7	-	-	-	-	
			2.7	-	-	-	-	
			3.0 to 3.6	-	1.0	-	1.0	

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

^{5.} These values of V_I are used to test DC electrical characteristics only.

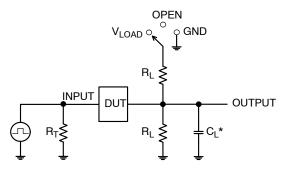
DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25 °C		3	
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 7)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		0.8		٧
V _{OLV}	Dynamic LOW Valley Voltage (Note 7)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		0.8		V

^{7.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

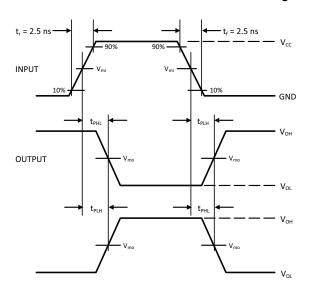
Symbol	Parameter	Condition	Тур	Unit
C _{IN}	Input Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	7	pF
C _{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	25	pF

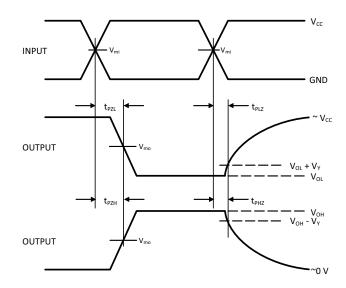


Test	Switch Position
t _{PLH} / t _{PHL}	Open
t _{PLZ} / t _{PZL}	V_{LOAD}
t _{PHZ} / t _{PZH}	GND

 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$ f = 1 MHz

Figure 3. Test Circuit





V _{CC} , V	R_L, Ω	C _L , pF	V_{LOAD}	V _{mi} , V	V _{mo} , V	V _Y , V
1.65 to 1.95	500	30	2 x V _{CC}	V _{CC} /2	V _{CC} /2	0.15
2.3 to 2.7	500	30	2 x V _{CC}	V _{CC} /2	V _{CC} /2	0.15
2.7	500	50	6 V	1.5	V _{CC} /2	0.3
3.0 to 3.6	500	50	6 V	1.5	V _{CC} /2	0.3
4.5 to 4.5	500	50	2 x V _{CC}	V _{CC} /2	V _{CC} /2	0.3

Figure 4. Switching Waveforms

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MC74LCX240DTR2G	LCX 240	TSSOP-20 (Pb-Free)	2500 Tape & Reel
MC74LCX240DWR2G	LCX240	SOIC-20 WB (Pb-Free)	1000 Tape & Reel

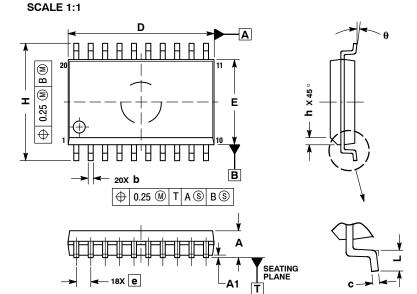
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D.</u>





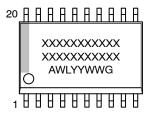
SOIC-20 WB CASE 751D-05 **ISSUE H**

DATE 22 APR 2015



- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
b	0.35	0.49	
С	0.23	0.32	
D	12.65	12.95	
E	7.40	7.60	
е	1.27 BSC		
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
A	0 °	7 °	



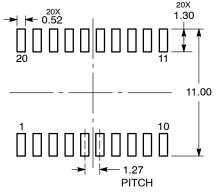
GENERIC MARKING DIAGRAM*

XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

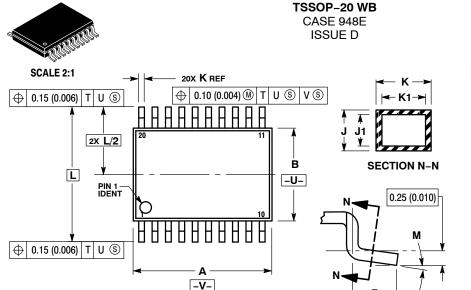
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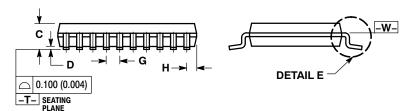
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^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DATE 17 FEB 2016







DETAIL E

NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

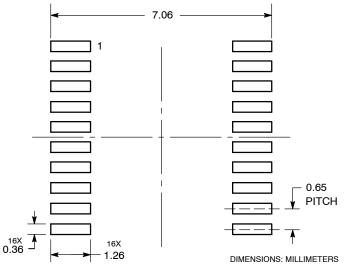
 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE
- DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
 TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

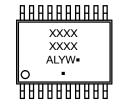
	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

RECOMMENDED SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ", may or may not be present. Some products may not follow the Generic Marking.

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